

irradiating the separable layer with light to cause a separation, such that the second thin film device layer is transferred to the first substrate, and formed on the first thin film device layer

2. (Four Times Amended) A method of forming a three-dimensional device, the device including at least a first thin film device layer and a second thin film device layer constituting a three-dimensional circuit, each thin film device layer deposited in a thickness direction, each thin film device layer constituting a circuit disposed in a predetermined region extending in a planar direction, the method comprising:

depositing the second thin film device layer by a separation in a separable layer on which the second thin film device layer is formed.

3. (Four Times Amended) The method of forming a three-dimensional device according to claim 1, further comprising irradiating the separable layer with light to cause a separation in at least one of the separable layer and at an interface between the separable layer and the second substrate so that the second thin film device layer on the second substrate is transferred to the first substrate of the three-dimensional device.

12. (Three Times Amended) The method of forming a three-dimensional device according to claim 1, the second thin film device layer deposited by transferring being formed simultaneously with at least one other of the thin film device layers.

17. (Three Times Amended) The method of forming a three-dimensional device according to claim 16, the logic circuit being capable of driving the memory cell array.

21. (Twice Amended) A method for manufacturing a three-dimensional device having a plurality of thin film device layers on a first substrate, the plurality of thin film device layers including at least a first thin film device layer and a second thin film device layer, the method comprising: